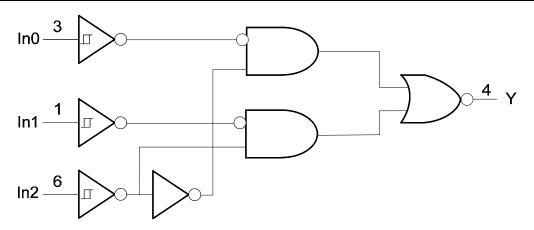


Pin Descriptions

Pin Name	Function
IN1	Data Input
GND	Ground
IN0	Data Input
Υ	Data Output
V _{CC}	Supply Voltage
IN2	Data Input

Logic Diagram

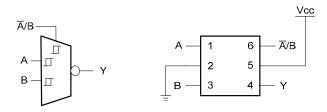


Function Table

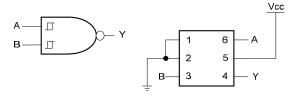
	Inputs		Output
IN2	IN1	Υ	
L	لــ	L	Н
L	┙	Н	H
L	Н	L	L
L	Н	Н	لــ
Н	L	L	Н
Н	L	Н	L
Н	Н	L	Н
Н	Н	Н	L



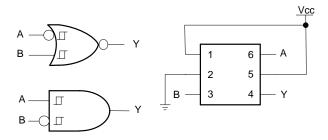
Logic Configurations



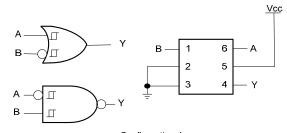
Configuration 1
2 to 1 Data Selector with Inverted Output



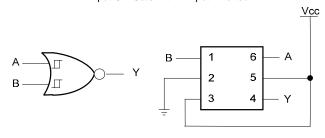
Configuration 2
2-Input NAND Gate
2-Input OR Gate with Both Inputs Inverted



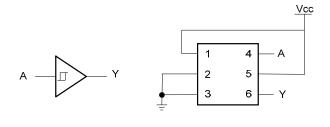
Configuration 3
2-Input NAND Gate with B Input Inverted
2-Input OR Gate with A Input Inverted



Configuration 4
2-Input OR Gate with One Input Inverted
2-Input NAND Gate with One Input Inverted



Configuration 5 2-Input NOR Gate



Configuration 6 Buffer

Function Selection Table							
Logic Function	Configuration						
2-to-1 Data Selector with inverted output	1						
2-input NAND gate	2						
2-input AND with inverted input	3						
2-input NOR with inverted input	3						
2-input NAND with one inverted input	4						
2-input OR with one inverted input	4						
2-input NOR	5						
1-input Buffer	6						



Absolute Maximum Ratings (Note 4)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to +6.5	V
VI	Input Voltage Range	-0.5 to +6.5	V
Vo	Voltage applied to output in high impedance or IOFF state	-0.5 to +6.5	V
Vo	Voltage applied to output in high or low state	-0.3 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current V _I <0	-50	mA
lok	Output Clamp Current	-50	mA
lo	Continuous output current	±50	mA
	Continuous current through Vdd or GND	±100	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Notes:

Recommended Operating Conditions (Note 5)

Symbol		Parameter	Min	Max	Unit	
	On and the milder of	Operating	1.65	5.5	V	
V _{CC}	Operating Voltage	Data retention only	1.5		V	
VI	Input Voltage		0	5.5	V	
Vo	Output Voltage		0	V _{CC}	V	
		V _{CC} = 1.65V		-4		
		V _{CC} = 2.3V		-8		
I _{OH}	High-level output current	V 0V		-16	mA	
		$V_{CC} = 3V$		-24		
		V _{CC} = 4.5V		-32		
		V _{CC} = 1.65V		4		
		V _{CC} = 2.3V		8		
I _{OL}	Low-level output current	W 8W		16	mA	
		Vcc = 3V		24		
		V _{CC} = 4.5V		32		
		$V_{CC} = 1.8V \pm 0.15V, 2.5V \pm 0.2V$		20		
Δt/ΔV	Input transition rise or fall rate	$V_{CC} = 3.3V \pm 0.3V$		10	ns/V	
		V _{CC} = 5 V ± 0.5V		5		
T _A	Operating free-air temperature		-40	+125	°C	

Notes: 5. Unused inputs should be held at V_{CC} or Ground.

^{4.} Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.



Electrical Characteristics $T_A = -40$ °C to +85°C (All typical values are at $V_{CC} = 3.3$ V, $T_A = +25$ °C)

Symbol	Parameter	Test Conditions	Vcc	Min	Тур.	Max	Unit
			1.65V	0.70		1.20	
	5 11 1 1		2.3V	1.11		1.60	
V_{T+}	Positive-going input threshold voltage		3V	1.50		2.00	
	tilleshold voltage		4.5V	2.16		2.74	
			5.5V	2.61		3.33	
			1.65V	0.30		0.72	
			2.3V	0.58		1.00	
V_{T-}	Negative-going input threshold voltage		3V	0.80		1.30	
	threshold voltage		4.5V	1.21		1.95	
			5.5V	1.45		2.35	
			1.65V	0.30		0.62	
	Hysteresis (V _{T+} - V _{T-)}		2.3V	0.40		0.80	
ΔV_{T}			3V	0.35		1.00	
			4.5V	0.55		1.10	
			5.5V	0.60		1.20	
		I _{OH} = -100μA	1.65V to 5.5V	V _{CC} - 0.1			
		I _{OH} = -4mA	1.65V	1.2			
.,		I _{OH} = -8mA	2.3V	1.9			
V_{OH}	High Level Output Voltage	I _{OH} = -16mA		2.4			V
		I _{OH} = -24mA	3V	2.3			
		I _{OH} = -32mA	4.5V	3.8			
		I _{OL} = 100μA	1.65V to 5.5V			0.1	
		I _{OL} = 4mA	1.65V			0.45	
.,		I _{OL} = 8mA	2.3V			0.3	
V_{OL}	High-level Input Voltage	I _{OL} = 16mA				0.4	V
		I _{OL} = 24mA	3V			0.55	
		I _{OL} = 32mA	4.5V			0.55	
lı	Input Current	V _I = 5.5V or GND	0 to 5.5V			± 5	μA
I _{OFF}	Power Down Leakage Current	V_I or $V_O = 5.5V$	0			± 10	μA
I _{CC}	Supply Current	V _I = 5.5V of GND I _O = 0	1.65V to 5.5V			10	μА
Δl _{CC}	Additional Supply Current	One input at V _{CC} -0.6V Other inputs at V _{CC} or GND	3V to 5.5V			500	μΑ



Electrical Characteristics $T_A = -40$ °C to +125°C (All typical values are at $V_{CC} = 3.3V$, $T_A = +25$ °C)

Symbol	Parameter	Test Conditions	V _{CC}	Min	Тур	Max	Unit
			1.65V	0.70		1.20	
			2.3V	1.11		1.60	
V_{T+}	Positive-going input threshold voltage		3V	1.50		2.00	
	lineshold voltage		4.5V	2.16		2.74	
			5.5V	2.61		3.33	
			1.65V	0.30		0.75	
			2.3V	0.58		1.03	
V_{T-}	Negative-going input threshold voltage		3V	0.80		1.33	
	lineshold voltage		4.5V	1.21		1.95	
			5.5V	1.45		2.35	
			1.65V	0.30		0.62	
	I btaa.ia		2.3V	0.37		0.80	
ΔV_{T}	Hysteresis (V _{T+} - V _{T-)}		3V	0.32		1.00	
	(VT+ - VT-)		4.5V	0.50		1.20	
			5.5V	0.55		1.40	
		I _{OH} = -100μA	1.65V to 5.5V	V _{CC} - 0.1			
		I _{OH} = -4mA	1.65V	0.95			V
.,		$I_{OH} = -8mA$	2.3V	1.7			
Vон	High Level Output Voltage	I _{OH} = -16mA	0) /	1.9			
		I _{OH} = -24mA	3V	2.0			
		I _{OH} = -32mA	4.5V	3.4			
		I _{OL} = 100μA	1.65V to 5.5V			0.1	
		I _{OL} = 4mA	1.65V			0.7	
.,		I _{OL} = 8mA	2.3V			0.45	.,
VoL	High-level Input Voltage	I _{OL} = 16mA	2) (0.6	V
		I _{OL} = 24mA	3V			0.8	
		I _{OL} = 32mA	4.5V			0.8	
II	Input Current	V _I = 5.5V or GND	0 to 5.5V			± 100	μA
I _{OFF}	Power Down Leakage Current	V_1 or $V_0 = 5.5V$	0			± 200	μA
Icc	Supply Current	V _I = 5.5V of GND I _O =0	1.65V to 5.5V			200	μΑ
ΔI _{CC}	Additional Supply Current	One input at V_{CC} -0.6V Other inputs at V_{CC} or GND	3V to 5.5V			5000	μΑ



Electrical Characteristics (All typical values are at $V_{CC} = 3.3V$, $T_A = +25$ °C)

Symbol	Parameter	Test Conditions	V _{CC}	Min	Тур	Max	Unit
C _I	Input Capacitance	$V_I = V_{CC} - or GND$	3.3		3.5		pF
		SOT26			204		
	Thermal Resistance Junction-	SOT363	(Note 6)		371		0000
θ _{JA}	to-Ambient	X2-DFN1410-6			430		°C/W
		X2-DFN1010-6			510		
		SOT26			52		
	Thermal Resistance Junction-	SOT363	(1)		143		0000
θις	to-Case	X2-DFN1410-6	(Note 6)		190		°C/W
		X2-DFN1010-6			250		

Notes:

Switching Characteristics

 $T_A = -40$ °C to +85°C, $C_L = 30$ or 50pF as noted (see Figure 1)

Parameter	From	TO (OUTPUT)	V _{CC} = 1.8V ± 0.15V				V _{CC} = 3.3V ± 0.3V		V _{CC} = 5V ± 0.5V		Unit
	(Input)	(OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	
t _{pd}	Any	Υ	1.0	14.4	0.7	8.3	0.7	6.3	0.7	5.1	ns

 $T_A = -40$ °C to +125°C, $C_L = 30$ or 50pF as noted (see Figure 1)

Parameter	From	TO (OUTPUT)	V _{CC} = ± 0.	: 1.8V .15V		: 2.5V).2V		: 3.3V).3V	~ ~	= 5V).5V	Unit
	(Input)	(OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	
t _{pd}	Any	Υ	1.0	18.0	0.7	10.4	0.7	7.9	0.7	6.4	ns

Operating Characteristics

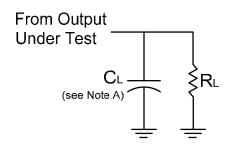
 $T_A = +25$ °C

	Parameter	Test	V _{CC} = 1.8V	V _{CC} = 2.5V	V _{CC} = 3.3V	V _{CC} = 5V	Unit	
		Conditions Typ		Тур	Тур	Тур		
C _{pd}	Power dissipation capacitance	f = 10 MHz	22	22	23	24	pF	

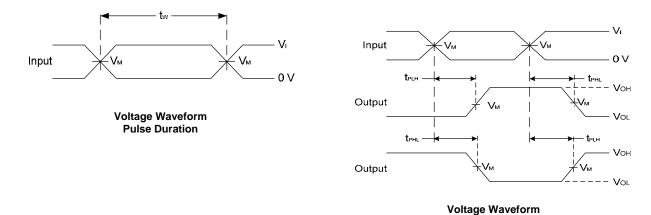
^{6.} Test condition for SOT26, SOT363, X2-DFN1410-6 and X2-DFN1010-6: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



Parameter Measurement Information



V	Inj	outs	V		R _L	
V _{CC}	VI	t _r /t _f	V _M	CL		
1.8V±0.15V	V _{CC}	≤2ns	V _{CC} /2	30pF	1ΚΩ	
2.5V±0.2V	Vcc	≤2ns	V _{CC} /2	30pF	500Ω	
3.3V±0.3V	3V	≤2.5ns	1.5V	50pF	500Ω	
5V±0.5V	V _{CC}	≤2.5ns	V _{CC} /2	50pF	500Ω	



Propagation Delay Times Inverting and Non Inverting Outputs

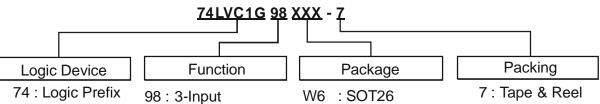
Figure 1. Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

- B. All pulses are supplied at pulse repetition rate ≤ 10 MHz
- C. Inputs are measured separately one transition per measurement
- D. t_{PLH} and t_{PHL} are the same as t_{PD}



Ordering Information



LVC: 1.65 to 5.5V Configurable DW: SOT363

Family Multiple-Function FW4: X2-DFN1010-6 1G: One gate Gate FZ4: X2-DFN1410-6

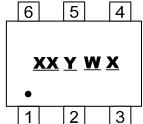
	Burlium On I	Darella va Carla	Packaging	7" Tape and Reel	
	Device	Package Code	(Note 7)	Quantity	Part Number Suffix
Po	74LVC1G98W6-7	W6	SOT26	3000/Tape & Reel	-7
Po	74LVC1G98DW-7	DW	SOT363	3000/Tape & Reel	-7
Pb ,	74LVC1G98FW4-7	FW4	X2-DFN1010-6	5000/Tape & Reel	-7
Pb	74I VC1G98F74-7	F74	X2-DFN1410-6	5000/Tape & Reel	-7

Notes: 7. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



Marking Information

(1) SOT26, SOT363



74LVC1G98DW

XX: Identification code

Y: Year 0~9

W: Week: A~Z: 1~26 week;

a~z: 27~52 week; z represents

52 and 53 week X: A~Z: Internal Code

Part Number	Package	Identification Code
74LVC1G98W6	SOT26	TZ

SOT363

(2) X2-DFN1010-6, X2-DFN1410-6

(Top View)



XX: Identification Code

Y : Year : 0~9

W: Week: A~Z: 1~26 week; a~z: 27~52 week; z represents

ΤZ

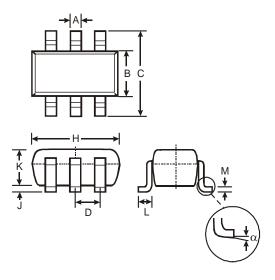
52 and 53 week X: A~Z: Internal code

Part Number	Package	Identification Code
74LVC1G98FW4	X2-DFN1010-6	TZ
74LVC1G98Z4	X2-DFN1410-6	TZ



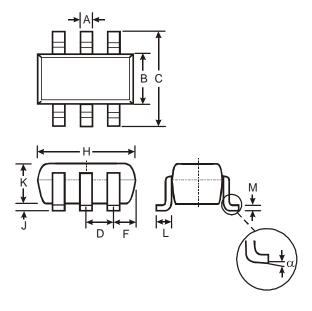
Package Outline Dimensions (All Dimensions in mm)

(1) SOT26



SOT26				
Dim	Min	Max	Тур	
Α	0.35	0.50	0.38	
В	1.50	1.70	1.60	
U	2.70	3.00	2.80	
D	_		0.95	
Н	2.90	3.10	3.00	
7	0.013	0.10	0.05	
K	1.00	1.30	1.10	
L	0.35	0.55	0.40	
М	0.10	0.20	0.15	
α	0°	8°	_	
All Dimensions in mm				

(2) SOT363

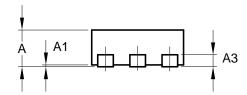


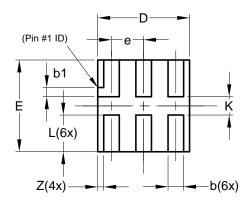
SOT363				
Dim	Min	Max		
Α	0.10	0.30		
В	1.15	1.35		
C	2.00	2.20		
D	0.65	Тур		
F	0.40	0.45		
H	1.80	2.20		
J	0	0.10		
K	0.90	1.00		
Г	0.25	0.40		
М	0.10	0.22		
α	0°	8°		
All Dimensions in mm				



Package Outline Dimensions (All Dimensions in mm)

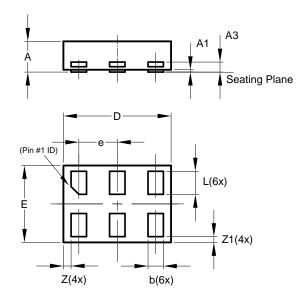
(3) X2-DFN1010-6





X2-DFN1010-6				
Dim	Min	Max	Тур	
Α		0.40	0.39	
A 1	0.00	0.05	0.02	
А3			0.13	
b	0.14	0.20	0.17	
b1	0.05	0.15	0.10	
D	0.95	1.05	1.00	
Е	0.95	1.05	1.00	
е			0.35	
L	0.35	0.45	0.40	
K	0.15			
Z			0.065	
All Dimensions in mm				

(4) X2-DFN1410-6

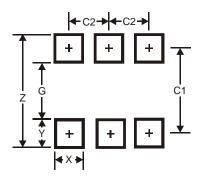


X2-DFN1410-6				
Dim	Min	Max	Тур	
Α		0.40	0.39	
A1	0.00	0.05	0.02	
А3		_	0.13	
b	0.15	0.25	0.20	
D	1.35	1.45	1.40	
Е	0.95	1.05	1.00	
е		_	0.50	
L	0.25	0.35	0.30	
Z		_	0.10	
Z 1	0.045	0.105	0.075	
All Dimensions in mm				



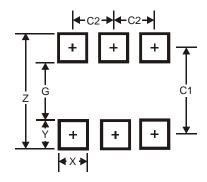
Suggest Pad Layout

(1) SOT26



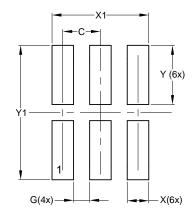
Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.95

(2) SOT363



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Y	0.6
C1	1.9
C2	0.65

(3) X2-DFN1010-6

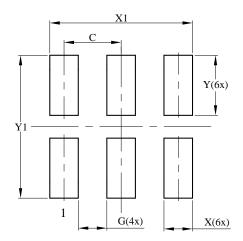


Dimensions	Value (in mm)
С	0.350
G	0.150
Х	0.200
X1	0.900
Y	0.550
Y1	1.250



Suggest Pad Layout

(4) X2-DFN1410-6



Dimensions	Value
Dilliensions	(in mm)
С	0.500
G	0.250
Х	0.250
X1	1.250
Υ	0.525
Y1	1.250

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